

Attorney's Docket No.: 07977/082003/US3141D1D1

In the claims:

Please cancel claim 1.

Please add the following new claims.

{1. (Cancelled)}

2. (New) A method for manufacturing a semiconductor device comprising:

C¹ introducing a first gas into a reaction chamber;
applying an RF power having a first voltage between electrodes in the reaction chamber to form a plasma of the first gas;

increasing the voltage of the RF power from the first voltage to a second voltage higher than the first voltage;

introducing a second gas into the reaction chamber after or simultaneously when the voltage of the RF power reaches the second voltage, the second gas comprising a different material from the first gas;

forming an insulating film over a substrate from the first and second gases through plasma CVD in the reaction chamber.

3. (New) A method for manufacturing a semiconductor device comprising:

introducing a first gas into a reaction chamber;

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applying an RF power having a first voltage to the first gas in order to form a plasma of the first gas;

increasing the voltage of the RF power from the first voltage to a second voltage higher than the first voltage;

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introducing a second gas into the reaction chamber after or simultaneously when the voltage of the RF power reaches the second voltage, the second gas comprising a different material from the first gas;

forming a film over a substrate from the first and second gases through plasma CVD in the reaction chamber.

4. (New) A method for manufacturing a semiconductor device comprising:

introducing a first gas into a reaction chamber;

applying an RF power having a first voltage to the first gas in order to form a plasma of the first gas;

increasing the voltage of the RF power from the first voltage to a second voltage higher than the first voltage;

introducing a second gas into the reaction chamber after or simultaneously when the voltage of the RF power reaches the second voltage, the second gas comprising a different material from the first gas;

forming an insulating film over a substrate from the first and second gases through plasma CVD in the reaction chamber,

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wherein the substrate comprises a silicon wafer.

5. (New) A method for manufacturing a semiconductor device comprising:

introducing a first gas into a reaction chamber;

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applying an RF power having a first voltage between electrodes in the reaction chamber to form a plasma of the first gas;

increasing the voltage of the RF power from the first voltage to a second voltage higher than the first voltage;

introducing a second gas into the reaction chamber after or simultaneously when the voltage of the RF power reaches the second voltage, the second gas comprising a different material from the first gas;

forming an insulating film over a substrate from the first and second gases through plasma CVD in the reaction chamber,

wherein the substrate comprises a silicon wafer.

6. (New) A method for manufacturing a semiconductor device comprising:

introducing a first gas into a reaction chamber;

applying an RF power having a first voltage to the first gas in order to form a plasma of the first gas;

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increasing the voltage of the RF power from the first voltage to a second voltage higher than the first voltage;

C¹ introducing a second gas into the reaction chamber after or simultaneously when the voltage of the RF power reaches the second voltage, the second gas comprising a different material from the first gas;

forming a film over a substrate from the first and second gases through plasma CVD in the reaction chamber,

wherein the substrate comprises a silicon wafer.

7. (New) A method for manufacturing a semiconductor device comprising:

introducing a first gas into a reaction chamber;

applying an RF power having a first voltage between electrodes in the reaction chamber to form a plasma of the first gas;

increasing the voltage of the RF power from the first voltage to a second voltage higher than the first voltage;

introducing a second gas into the reaction chamber after or simultaneously when the voltage of the RF power reaches the second voltage, the second gas comprising a different material from the first gas;

forming an insulating film over a substrate from the first and second gases through plasma CVD in the reaction chamber,

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wherein the substrate comprises a glass.

8. (New) A method for manufacturing a semiconductor device comprising:

introducing a first gas into a reaction chamber;

applying an RF power having a first voltage to the first gas in order to form a plasma of the first gas;

increasing the voltage of the RF power from the first voltage to a second voltage higher than the first voltage;

introducing a second gas into the reaction chamber after or simultaneously when the voltage of the RF power reaches the second voltage, the second gas comprising a different material from the first gas;

forming a film over a substrate from the first and second gases through plasma CVD in the reaction chamber

wherein the substrate comprises a glass.

9. (New) A method according to claim 2, wherein the first voltage of the RF power is a half or less of the second voltage.

10. (New) A method according to claim 3, wherein the first voltage of the RF power is a half or less of the second voltage.

11. (New) A method according to claim 4, wherein the first

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voltage of the RF power is a half or less of the second voltage.

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12. (New) A method according to claim 5, wherein the first voltage of the RF power is a half or less of the second voltage.

13. (New) A method according to claim 6, wherein the first voltage of the RF power is a half or less of the second voltage.

14. (New) A method according to claim 7, wherein the first voltage of the RF power is a half or less of the second voltage.

15. (New) A method according to claim 8, wherein the first voltage of the RF power is a half or less of the second voltage.

16. (New) A method according to claim 2, wherein the first gas comprises oxygen and the second gas comprises an organic silane.

17. (New) A method according to claim 3, wherein the first gas comprises oxygen and the second gas comprises an organic silane.

18. (New) A method according to claim 4, wherein the first gas comprises oxygen and the second gas comprises an organic

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silane.

19. (New) A method according to claim 5, wherein the first gas comprises oxygen and the second gas comprises an organic silane.

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20. (New) A method according to claim 6, wherein the first gas comprises oxygen and the second gas comprises an organic silane.

21. (New) A method according to claim 7, wherein the first gas comprises oxygen and the second gas comprises an organic silane.

22. (New) A method according to claim 8, wherein the first gas comprises oxygen and the second gas comprises an organic silane.

23. (New) A method according to claim 6, wherein the semiconductor device is an active matrix display device.

24. (New) A method according to claim 7, wherein the semiconductor device is an active matrix display device.

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25. (New) A method according to claim 8, wherein the semiconductor device is an active matrix display device.

Concluded
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26. (New) A method according to claim 6, wherein the semiconductor device is a liquid crystal display device.

27. (New) A method according to claim 7, wherein the semiconductor device is a liquid crystal display device.

28. (New) A method according to claim 8, wherein the semiconductor device is a liquid crystal display device.
